

IN THE SPECIFICATION:

Please replace paragraph number [0035] with the following rewritten paragraph:

[0035] Referring to drawing FIG. 4C, a portion of a semiconductor device 10 is shown having a bond pad 12 thereon having a copper layer 12' located thereon having a portion bonded thereto of a-conductor conductive lead-~~22 23~~ (numeral 22 previously referred to as "ball 22") located on a portion of a substrate 24 of a portion of a TAB tape 21. The surface 14 of substrate 11 of the semiconductor device 10 has a layer of insulation (typically a passivation layer of an insulating oxide or insulating nitride) 13 thereon. Also illustrated in drawing FIG. 4C, the function of the metal layer 12" is to provide a good metal to which an effective bond may be formed using well known bonding apparatus to the conductive lead-~~22 23~~ of the TAB tape 21. The conductive lead-~~22 23~~ of the TAB tape may be of any suitable metal, such as copper, copper alloys, etc. The metal layer 12" may be of any suitable metal, such as described herein.

Please replace paragraph number [0036] with the following rewritten paragraph:

[0036] Referring to drawing FIG. 4D, a portion of a semiconductor device 10 is shown having a bond pad 12 thereon having a copper layer 12' located thereon having a barrier layer 12"" located thereon having, in turn, a metal layer 12" located thereon. The metal layer 12" of the bond pad 12 is bonded to a portion of a-conductor conductive lead-~~22 23~~ located on a portion of a substrate 24 of a portion of a TAB tape-~~20 21~~. The-conductor conductive lead-~~22 23~~ of the portion of the TAB tape 21 including a layer 26 of suitable metal located thereon for the bonding of the-conductor conductive lead-~~22 23~~ to the metal layer 12" of the bond pad 12 of the semiconductor device 10. The surface 14 of substrate 11 of the semiconductor device 10 has a layer of insulation (typically a passivation layer of an insulating oxide or insulating nitride) 13 thereon. Also illustrated in drawing FIG. 4D, the function of the metal layer 12" is to provide a good metal to which an effective bond may be formed using well known bonding apparatus to the metal layer 26 of the conductive lead-~~22 23~~ of the TAB tape 21. The substrate 24 and metal

layer 26 may be of any suitable metal for bonding purposes, such as gold, alloys of gold, etc. The conductive lead-22 23 of the TAB tape may be of any suitable metal, such as copper, copper alloys, etc. The metal layer 12" may be of any suitable metal, such as described herein. The barrier layer 12"" may be of any suitable metal or material, such as described herein.